2SB1400

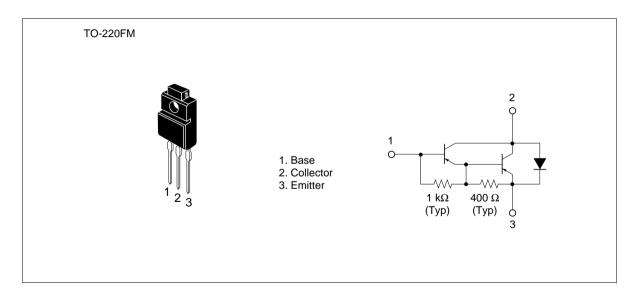
Silicon PNP Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline





2SB1400

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	-120	V	
Collector to emitter voltage	V_{CEO}	-120	V	
Emitter to base voltage	V_{EBO}	- 7	V	
Collector current	I _c	-6	Α	
Collector peak current	C(peak)	-10	А	
Collector power dissipation	P _c	2	W	
	P _C *1	25		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

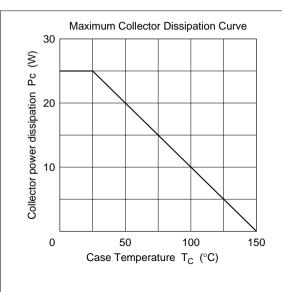
Note: 1. Value at $T_c = 25^{\circ}C$.

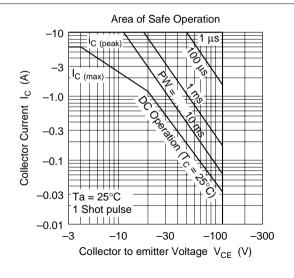
Electrical Characteristics (Ta = 25°C)

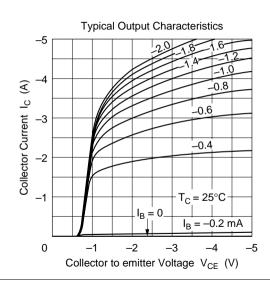
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	_	_	V	$I_{\rm C} = -0.1 \text{ mA}, I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{\rm C} = -25$ mA, $R_{\rm BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	_	_	V	$I_{\rm E} = -50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-10	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	-10	_	$V_{CE} = -100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -3 \text{ A}^{*1}$
Collector to emitter saturation	$V_{\text{CE}(\text{sat})1}$	_	_	-1.5	V	$I_{\rm C} = -3 \text{ A}, I_{\rm B} = -6 \text{ mA}^{*1}$
voltage	V _{CE(sat)2}	_	_	-3.0	_	$I_{\rm C} = -6 \text{ A}, I_{\rm B} = -60 \text{ mA}^{*1}$
Base to emitter saturation	V _{BE(sat)1}	_	_	-2.0	V	$I_{\rm C} = -3 \text{ A}, I_{\rm B} = -6 \text{ mA}^{*1}$
voltage	$V_{BE(sat)2}$	_	_	-3.5	_	$I_{\rm C} = -6 \text{ A}, I_{\rm B} = -60 \text{ mA}^{*1}$

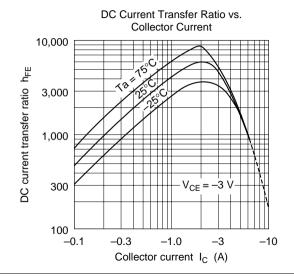
Note: 1. Pulse test.

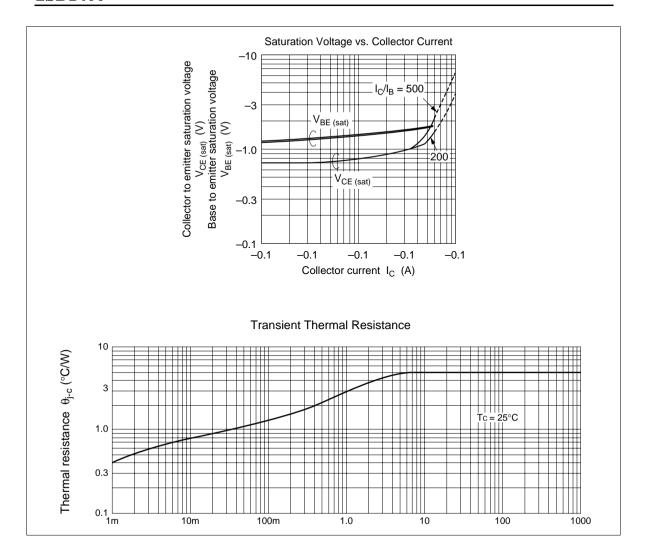
See switching characteristic curve of 2SB727(K).

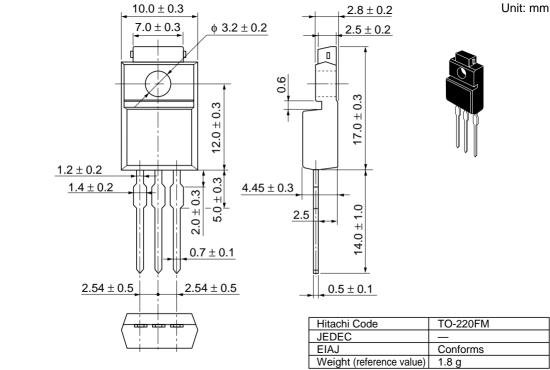












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